# B-3 SiC • Diamond • Other Related Materials

### **Representative Organizer**

Toru UJIHARA (Nagoya University)

#### <u>Co-organizers</u>

Hiroshi YANO (University of Tsukuba) Kazuhito KAMEI (NIPPON STEEL & SUMITOMO METAL CORPORATION) Isaho KAMATA (Central Research Institute of Electric Power Industry) Masashi KATO (Nagoya Institute of Technology) Kazutoshi KOJIMA (National Institute of Advanced Industrial Science and Technology) Yasuto HIJIKATA (Saitama University) Kenji UEDA (Nagoya University) Takeshi YOSHIKAWA (The University of Tokyo)

# Oral Session March 27 (Fri.) Room 2

Chair : Isaho Kamata (Central Research Institute of Electric Power Industry)

13:00	B3-I-01	<b>4H-SiC Bulk Growth Using High Temperature Gas Source Method</b> [Invited Lecture] <sup>1,2</sup> Jun Kojima, <sup>1,2</sup> Emi Makino, <sup>1,2</sup> Yuichiro Tokuda, <sup>1,2</sup> Naohiro Sugiyama, <sup>1,3</sup> Norihiro Hoshino, <sup>1,3</sup> Isaho Kamata,
		<sup>1,3</sup> Hidekazu Tsuchida
		1 R&D PARTNERSHIP FOR FUTURE POWER ELECTRONICS TECHNOLOGY 2 DENSO CORPORATION
		3 CENTRAL RESEARCH INSTITUTE OF ELECTRIC POWER INDUSTRY (CRIEPI)
13:30	B3-I-02	Radiation Response of Silicon Carbide Metal-Oxide-Semiconductor Transistors in High Dose
		Region [Invited Lecture]
		<sup>1</sup> <u>Takeshi Ohshima</u> , <sup>1,2</sup> T.Yokoseki, <sup>1,2</sup> K.Murata, <sup>1,2</sup> T.Matsuda, <sup>1,2</sup> S.Mitomo, <sup>1</sup> H.Abe, <sup>1</sup> T.Makino, <sup>1</sup> S.Onoda, <sup>2</sup> Y.Hijikata, <sup>3</sup> Y.Tanaka, <sup>3</sup> M.Kandori, <sup>3</sup> S.Okubo, <sup>3</sup> T.Yoshie
		1 JAPAN ATOMIC ENERGY AGENCY
		2 SAITAMA UNIVERSITY 3 SANKEN ELECTRIC CO., LTD.
14:00	B3-O-01	Correlation Between Grown Polytypes and Activity Ratio During Solution Growth of SiC
		with Multi-Component Solvent
		Atsushi Horio, <u>Shunta Harada</u> , Daiki Koike, Kenta Murayama, Kenta Aoyagi, Takenobu Sakai, Miho Tagawa, Toru Ujihara
		DEPARTMENT OF MATERIALS SCIENCE AND ENGINEERING, NAGOYA UNIVERSITY
14:15	B3-O-02	High Speed 4H-SiC Bulk Growth Under High Source Gas Concentration Using High Temperature Gas Source Method
		<sup>1,2</sup> <u>Vuichiro Tokuda</u> , <sup>1,2</sup> Emi Makino, <sup>1,2</sup> Naohiro Sugiyama, <sup>3</sup> Norihiro Hoshino, <sup>1,2</sup> Jun Kojima, <sup>3</sup> Hidekazu Tsuchida
		I R&D PARTNERSHIP FOR FUTURE POWER ELECTRONICS TECHNOLOGY
		3 DENSO CORPORATION
		2 CENTRAL RESEARCH INSTITUTE OF ELECTRIC POWER INDUSTRY (CRIEPI)
14:30	B3-O-03	Influence of Growth Pressure on Filling 4H-SiC Trenches by CVD Method
		<sup>1</sup> <u>Shiyang Ji</u> , <sup>1,2</sup> Kazutoshi Kojima, <sup>1,2</sup> Ryoji Kosugi, <sup>2</sup> Shingo Saito, <sup>2</sup> Yuuki Sakuma, <sup>1,2</sup> Yasunori Tanaka, <sup>2</sup> Sadafumi Yoshida, <sup>1</sup> Hiroaki Himi, <sup>2</sup> Hajime Okumura
		1 R&D PARTNERSHIP FOR FUTURE POWER ELECTRONICS TECHNOLOGY
		2 ADPERC, NATIONAL INSTITUTE OF ADVANCED INDUSTRIAL SCIENCE AND TECHNOLOGY
14:45	B3-O-04	Spectral Response, Carrier Lifetime and Photocurrents of SiC Photocathodes
		Masashi Kato, Keiko Miyake, Masaya Ichimura
		DEPARTMENT OF ENGINEERING PHYSICS, ELECTRONICS AND MECHANICS, NAGOYA INSTITUTE OF TECHNOLOGY
15:00		Break

## Chair : Kenji Ueda (Nagoya University)

15:15	B3-I-03	Diamond FETs Using Heterojunction and High-k Dielectrics [Invited Lecture]
		<sup>1,2</sup> Yasuo Koide, <sup>3</sup> Jiangwei Liu, <sup>1</sup> Masataka Imura, <sup>1</sup> Meiyong Liao
		I WIDE BANDGAP MATERIALS GROUP, OPTICAL & ELECTRICAL MATERIALS UNIT, NATIONAL INSTITUTE FOR MATERIALS SCIENCE (NIMS) 2 RESERCH NETWORK AND FACILITIES SERVICES DIVISION, NIMS 3 INTERNATIONAL CENTER FOR YOUNG SCIENTISTS, NIMS
15:45	B3-O-05	Effects of Inpurity and Substrate Temperature on Diamond Growth <u>Hideaki Yamada</u> , Akiyoshi Chayahara, Yoshiaki Mokuno <i>DIRAMOND RESEARCH GROUP, AIST</i>
16:00	B3-O-06	<b>Cu/Diamond Schottky Diodes for High-Temperature and High-Power Applications</b> <u>Kenichi Ohtsuka</u> , Kenji Ueda, Shinya Aichi, Hidefumi Asano <i>GRADUATE SCHOOL OF ENGINEERING</i> , <i>NAGOYA UNIVERSITY</i>
16:15	B3-O-07	Electrically-Active Defects in Ge <sub>1-x</sub> Sn <sub>x</sub> Epitaxtial Layer <sup>1</sup> <u>Wakana Takeuchi</u> , <sup>1,2</sup> Takanori Asano, <sup>1</sup> Mituo Sakashita, <sup>1</sup> Osamu Nakatsuka, <sup>1</sup> Shigeaki Zaima, <i>1 GRADUATE SCHOOL OF ENGINEERING, NAGOYA UNIVERSITY</i> <i>2 RESEARCH FELLOW OF JAPAN SOCIETY FOR THE PROMOTION OF SCIENCE</i>
16:30	B3-O-08	Response to Visible Light in Amorphous Carbon Nitride Films Prepared by Reactive Sputtering <u>Masami Aono</u> , Tomo Harata, Nobuaki Kitazawa, Yoshihisa Watanabe DEPARTMENT OF MATERIALS SCIENCE AND ENGINEERING, NATIONAL DEFENSE ACADEMY